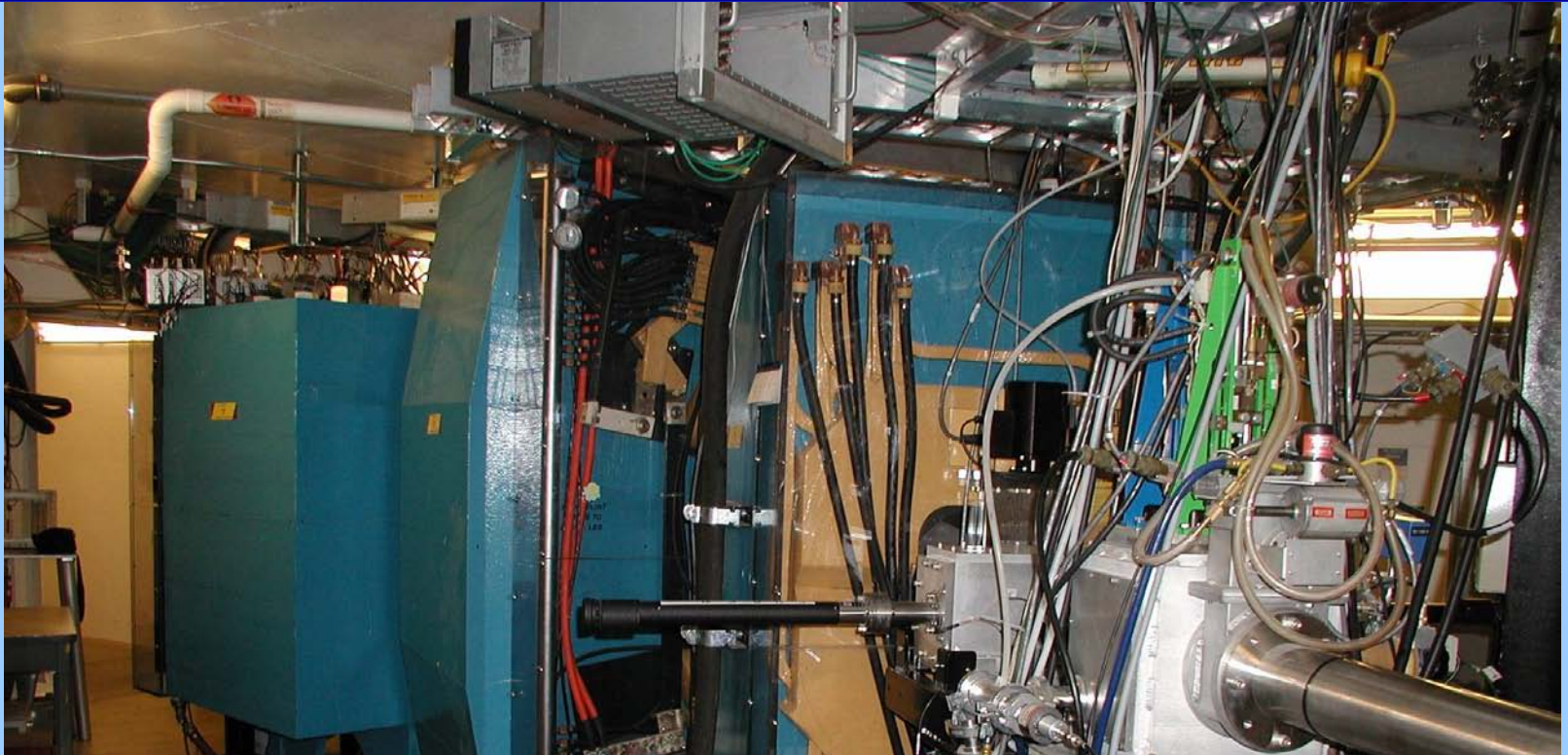
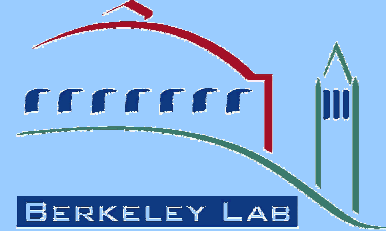


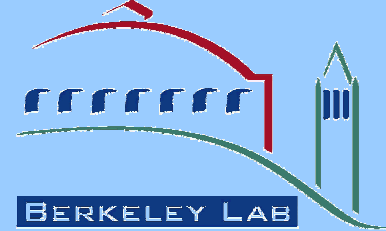
Berkeley Gas-Filled Separator Focal Plane and Beyond



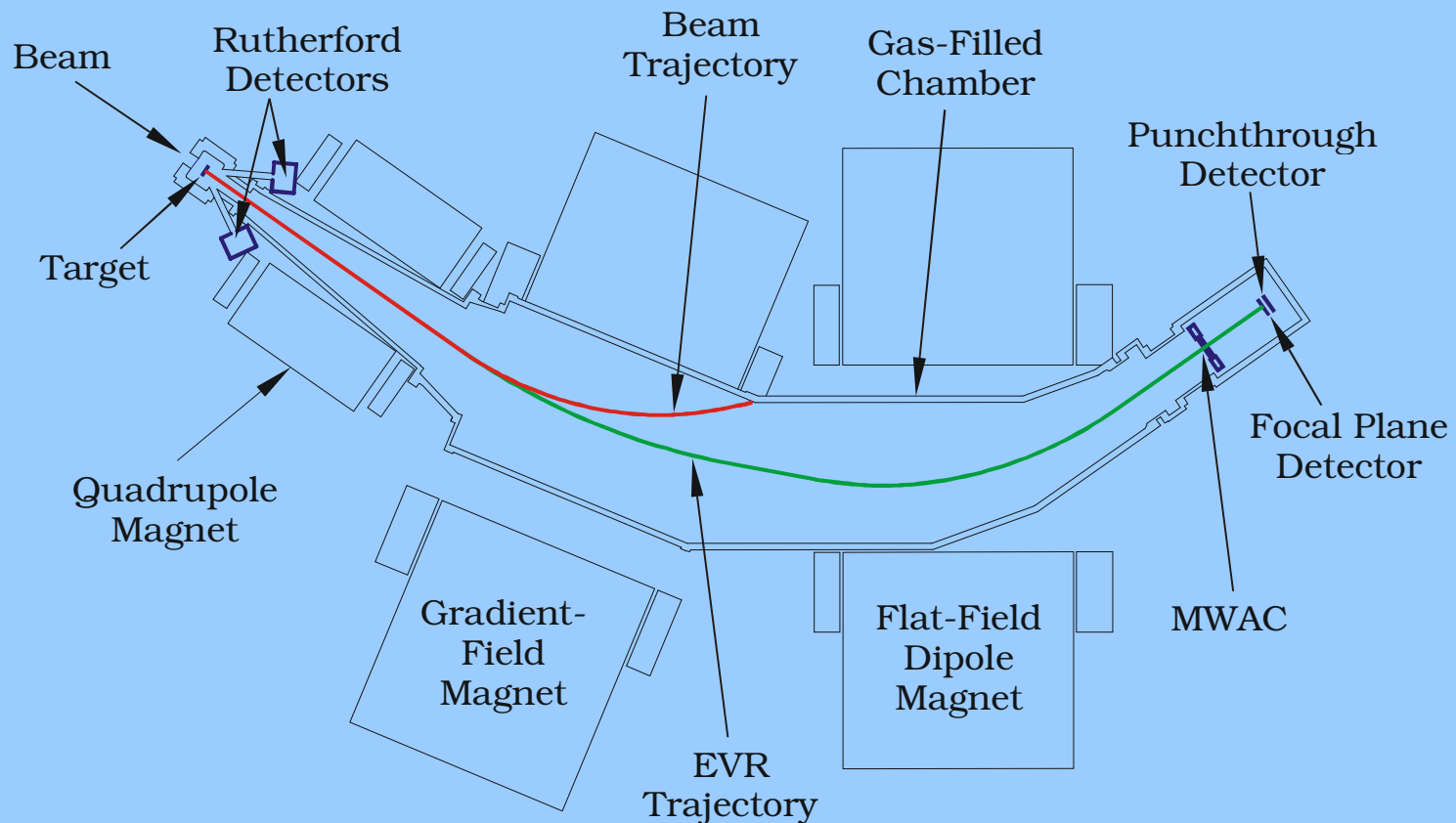
Ken Gregorich
Lawrence Berkeley National Laboratory

9th Workshop on
Recoil Separator for Superheavy Element Chemistry
GSI, Darmstadt, Germany
November 18, 2010

Stuff Behind the BGS



New BGS focal plane detector array GRETINA@BGS campaign Gas catcher, RFQ trap, and mass separator



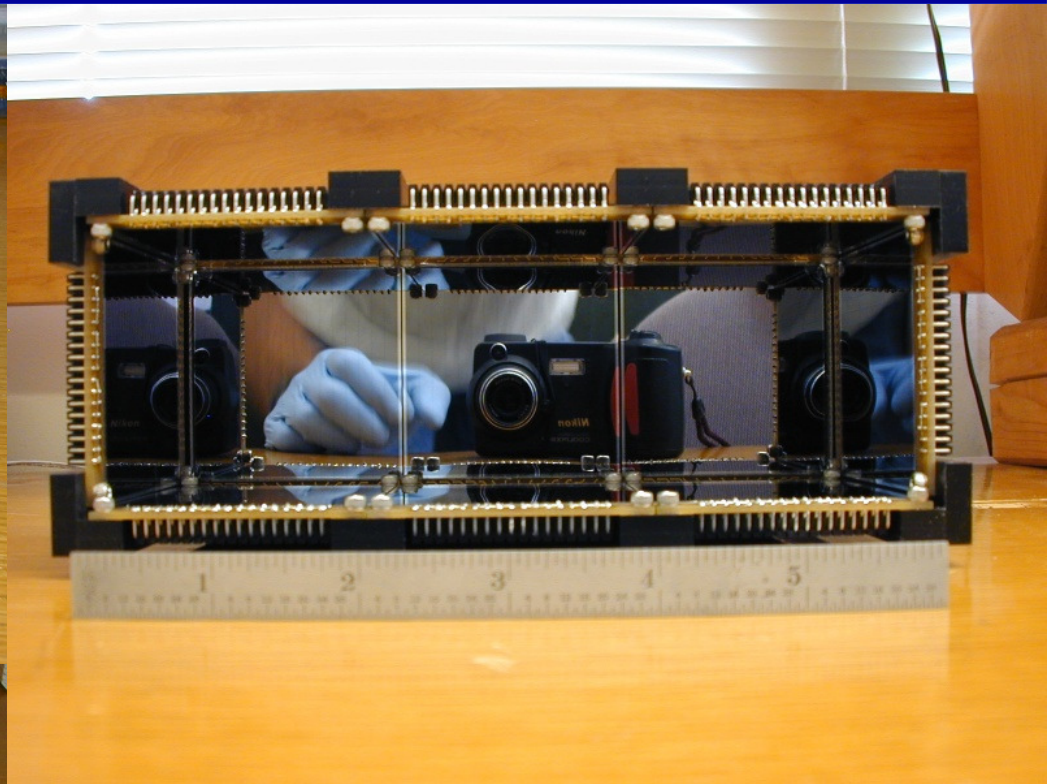
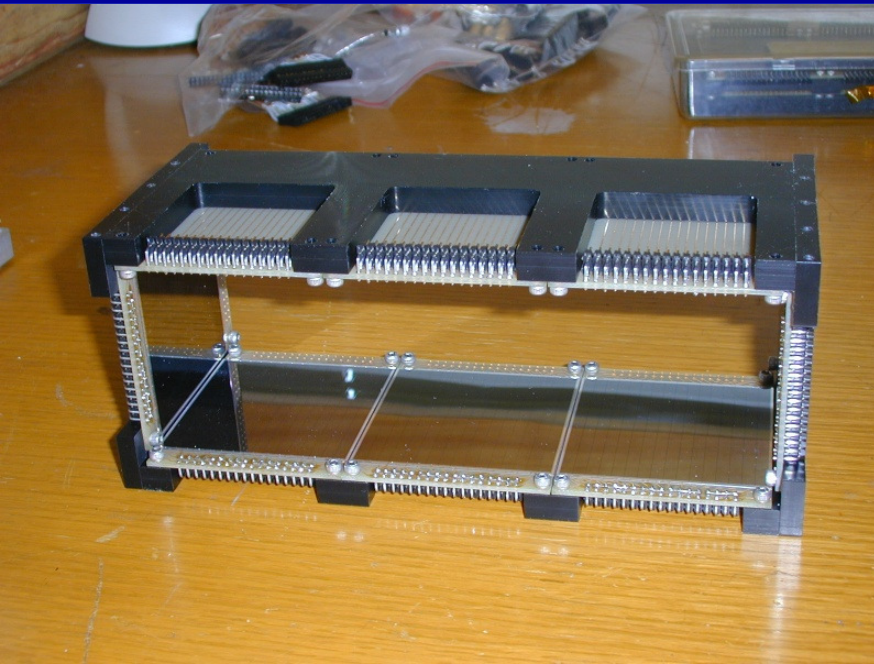
Present PSD Assembly



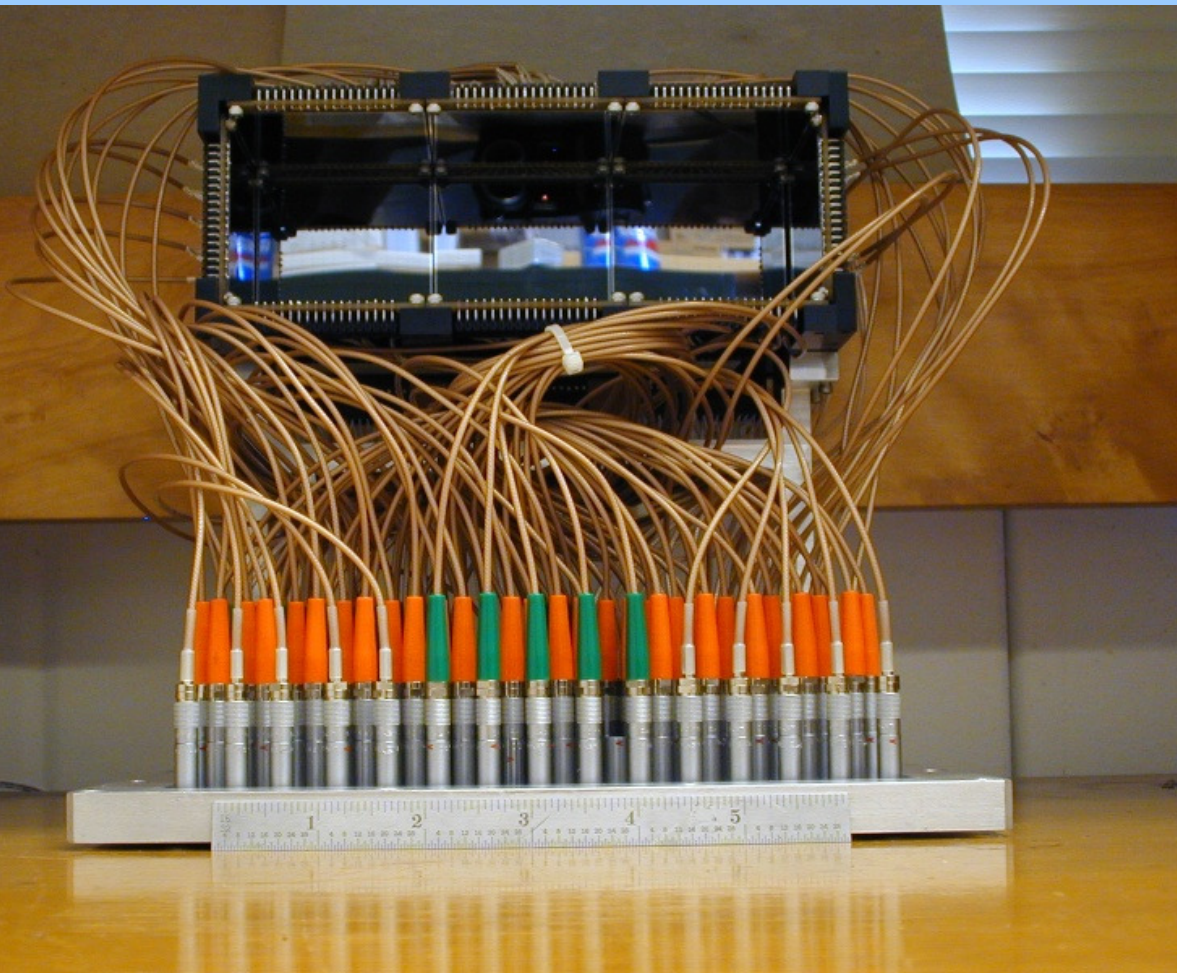
Focal plane is built from 3 6cm x 6cm chips
16 strips each with resistive charge division
~ 1000 effective “pixels”

Upstream box is built from 8 6cm x 6cm chips
32 sectors of 4 strips, no resistive charge division

Present PSD Assembly



Final Assembly of PSD array

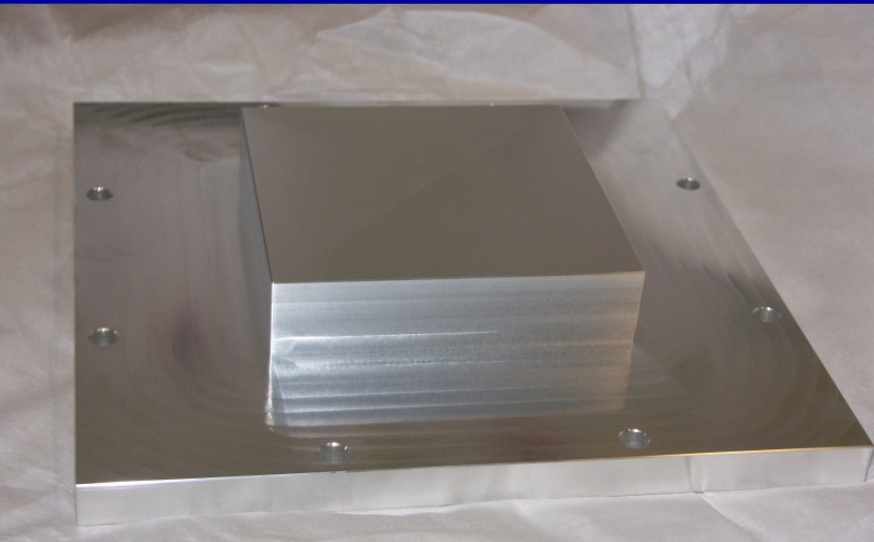


Recoil efficiency for
 $^{48}\text{Ca} + ^{238}\text{U} = 69\%$
(using 15mm w x 6mm h tgt)

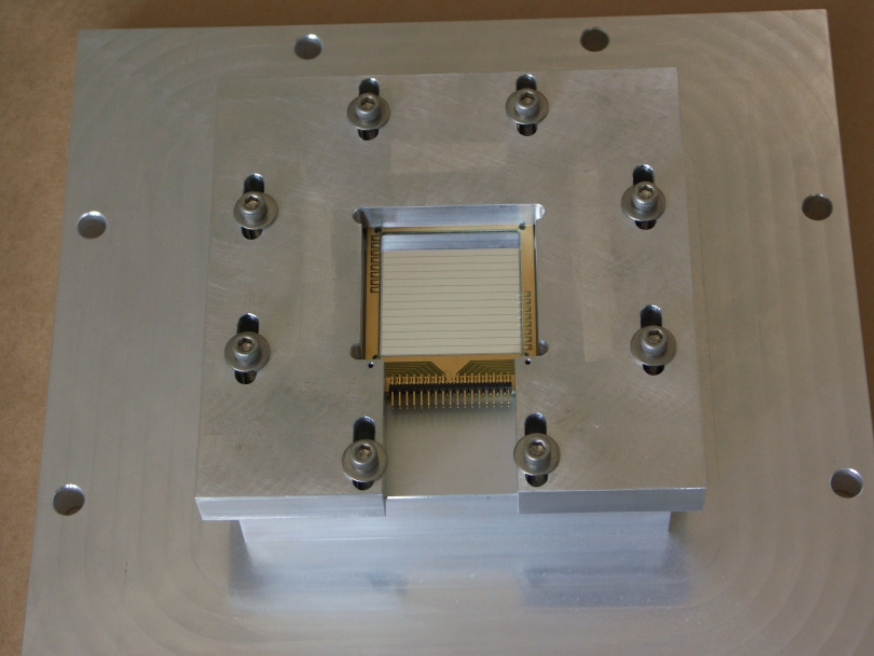
Alpha efficiency = 75%
(lower for shallow implants)

Conversion electron
efficiency is poor
 ~ 300 keV trigger level
 $\sigma_p \sim 1400$ keV*mm/E
300 μm thick Si

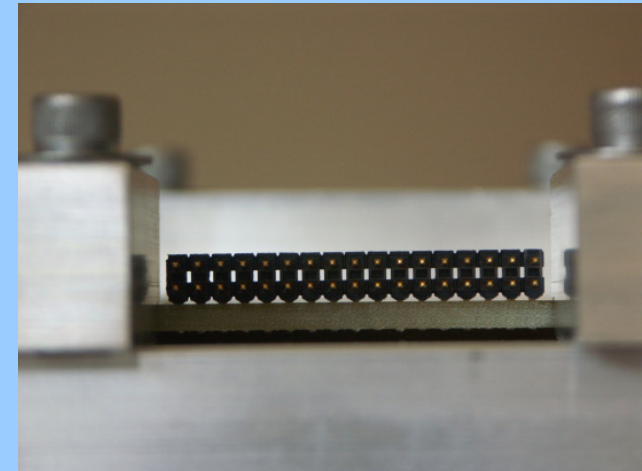
DSSD for K-isomer Studies



Re-entrant vacuum window for Ge clover
2-mm thick Al



DSSD mounted on inside of vacuum window
5 cm x 5 cm DSSD (Micron)
16 strips per side (**256 pixels**)
1-mm thick Si for good c.e. response



DSSD in place with Clover



Recoil efficiency ~ 35%

alpha efficiency = 50%

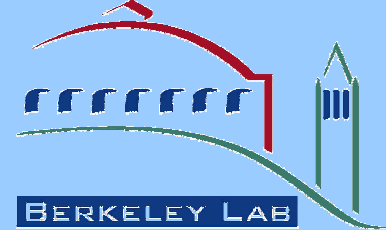
122 keV γ efficiency = 16%

900 keV γ efficiency = 4%

c.e. trigger threshold = 120 keV
(limited by SCR noise)

c.e. efficiency is large (1mm Si)

Paper Model of New DSSD configuration



Punchthru Detectors

3 x 64mm x 64mm DSSDs
used as SSSDs
32 strips per side
connected in groups of 3
gives a total of 32 signals
reject fast low-ionizing particles

Focal Plane Detectors

3 x 64mm x 64mm DSSDs
32 strips per side
connected in groups of 2
gives a total of 96 signals
and 3072 pixels
 α efficiency = 74%

Upstream Hexagonal Tunnel

6 x SSSDs
end trimmed to 35.2°
to fit against focal plane
4 strips per detector
total of 24 signals
increases α efficiency to 92%



3D Assembly Drawings of Focal Plane DSSSDs

1 mm thick Si
 32 strips/side (1024 pixels each chip)
 Mirror image configurations (for FP & punchthru)

010201501
 10/20/15
 10/20/15

Drawn: N.V. S.W.
 Checked: Dns.
 Date: 10/20/15
 Appd: [Signature]

Tolerances Unless Stated: Outputs Via: Sintered FTSH-133-21-F-D
 Package QD ± 0.1 mm: Mating connector: Sintered FTSH-133-21-F-D
 Package Hole ± 0.05 mm: Potted Wire Bonds: No
 Package Hole Pos'n ± 0.1 mm: Substrate Number: A-3628
 Deflector QD ± 20.0 μm: Substrate Material: 2 x 0.5 mm thick F88 sapphire wafers
 Connector Orientation: Exposed open side

Title: LBL BB7 Left PCB, 3D Assembly, Front and Rear View.

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Scale: N/A Dims In: mm Dwg No: C-2236

PCB Dimensions = 104.00 x 73.25 mm²
 Chip Dimensions = 67.975 x 67.975 mm²
 Active Area = 64.00 x 64.00 mm²

Front View

Rear View

Cut-out in ledge for rear guard ring connection

Outputs viewed from rear side

J = Front side strip
 O = Rear side strip

010201501
 10/20/15
 10/20/15

Drawn: N.V. S.W.
 Checked: Dns.
 Date: 10/20/15
 Appd: [Signature]

Tolerances Unless Stated: Outputs Via: Sintered FTSH-133-21-F-D
 Package QD ± 0.1 mm: Mating connector: Sintered FTSH-133-21-F-D
 Package Hole ± 0.05 mm: Potted Wire Bonds: No
 Package Hole Pos'n ± 0.1 mm: Substrate Number: A-3627
 Deflector QD ± 20.0 μm: Substrate Material: 2 x 0.5 mm thick F88 sapphire wafers
 Connector Orientation: Exposed open side

Title: LBL BB7 Right PCB, 3D Assembly, Front and Rear View.

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Scale: N/A Dims In: mm Dwg No: C-2237

PCB Dimensions = 104.00 x 73.25 mm²
 Chip Dimensions = 67.975 x 67.975 mm²
 Active Area = 64.00 x 64.00 mm²

Front View

Rear View

Cut-out in ledge for rear guard ring connection

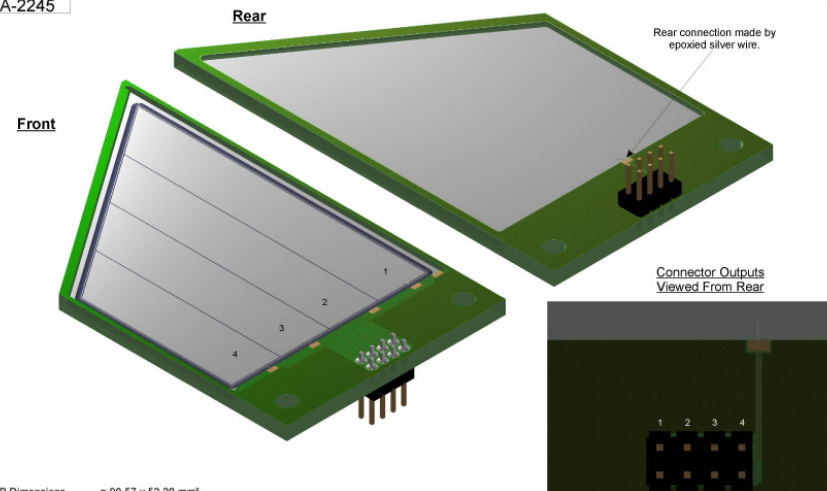
Outputs viewed from rear side

J = Front side strip
 O = Rear side strip

3D Assembly Drawings of Focal Plane SSSSDs

1 mm thick Si
 4 strips with no position sensitivity
 Mirror image configurations
 Specially shaped to fit against Cube Corner

Fig No A-2245

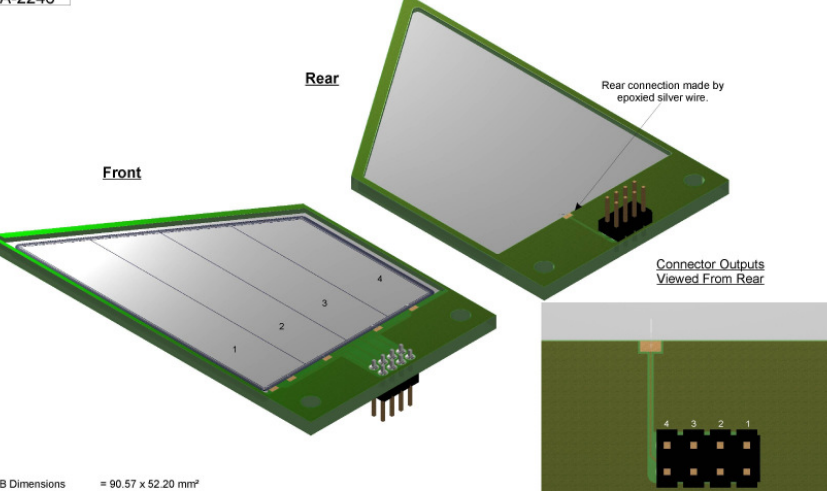


PCB Dimensions = 90.57 x 52.20 mm²
 Chip Dimensions = 74.56 x 50.40 mm²
 Active Area = 68.45 x 46.40 mm²

| | | | | | | | |
|--------|---------|------------|-----------------------------|-----------------------|-------------------------------|--------------|-------------------------|
| Drawn | Checked | Date | Tolerances Unless Stated | Outputs Via | Bartec Part Number | T8W104.08.L0 | Title |
| N.V.V. | S.W. | 04/11/2010 | Package OD ± 0.1 mm | Mating connector | Bartec Part Number | DS6-104.0.6 | LBL BB16 Left Hand PCB. |
| Des. | | | Package Hole ± 0.05 mm | Potted Wire Bonds | No | | 3D Assembly. |
| Appd. | | | Package Hole Pos'n ± 0.1 mm | Substrate Number | A-3648 | | Front and Rear View. |
| | | | Detector OD ± 20.0 µm | Substrate Material | 3.2 mm Thick FR4 PCB Material | | |
| | | | | Connector Orientation | Connector to Ext Rear Side | | |

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 graphics@micronsemiconductor.co.uk
 Scale N/A Dims In .mm Dwg No C-2245

Fig No A-2246

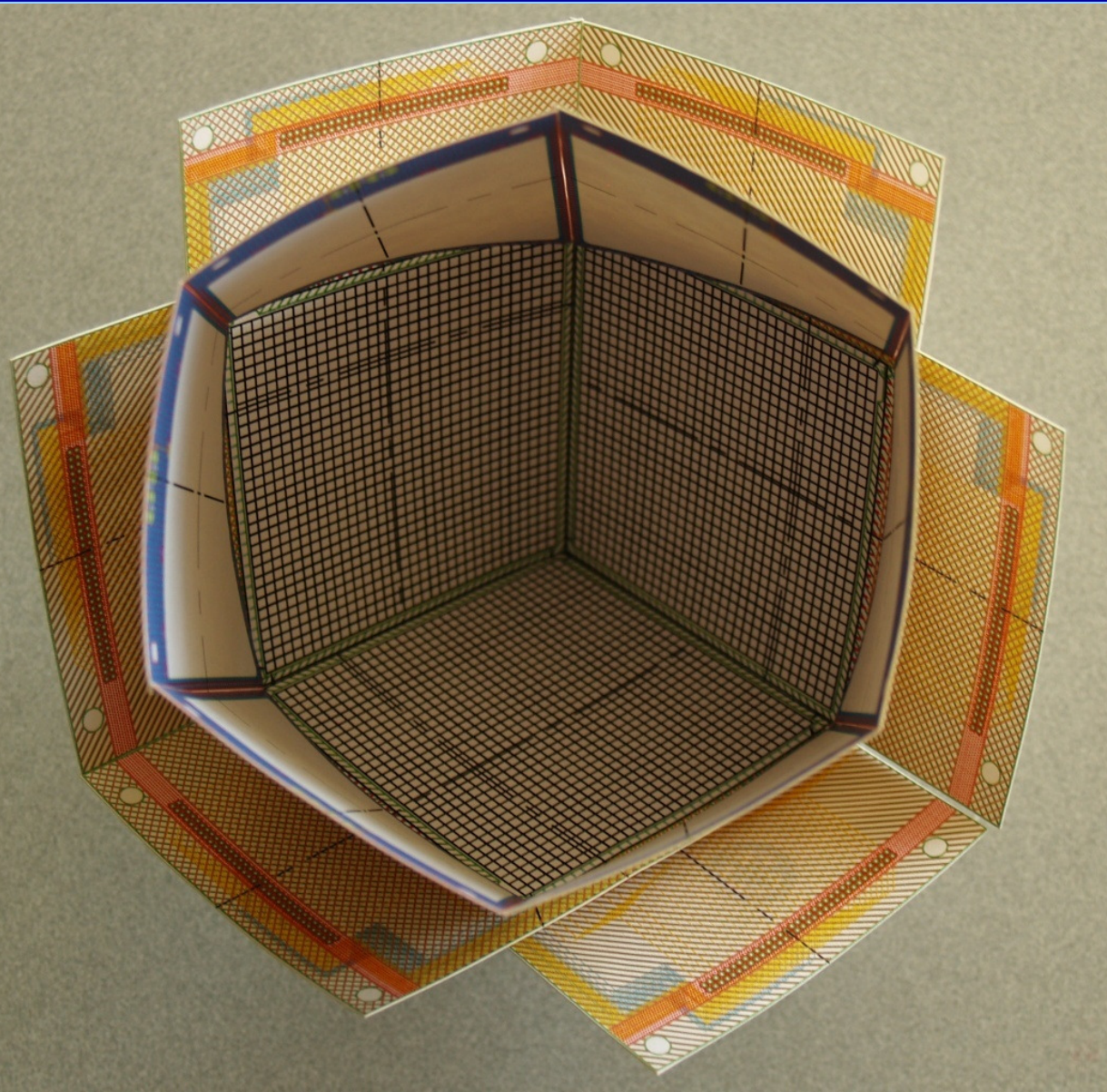


PCB Dimensions = 90.57 x 52.20 mm²
 Chip Dimensions = 74.56 x 50.40 mm²
 Active Area = 68.45 x 46.40 mm²

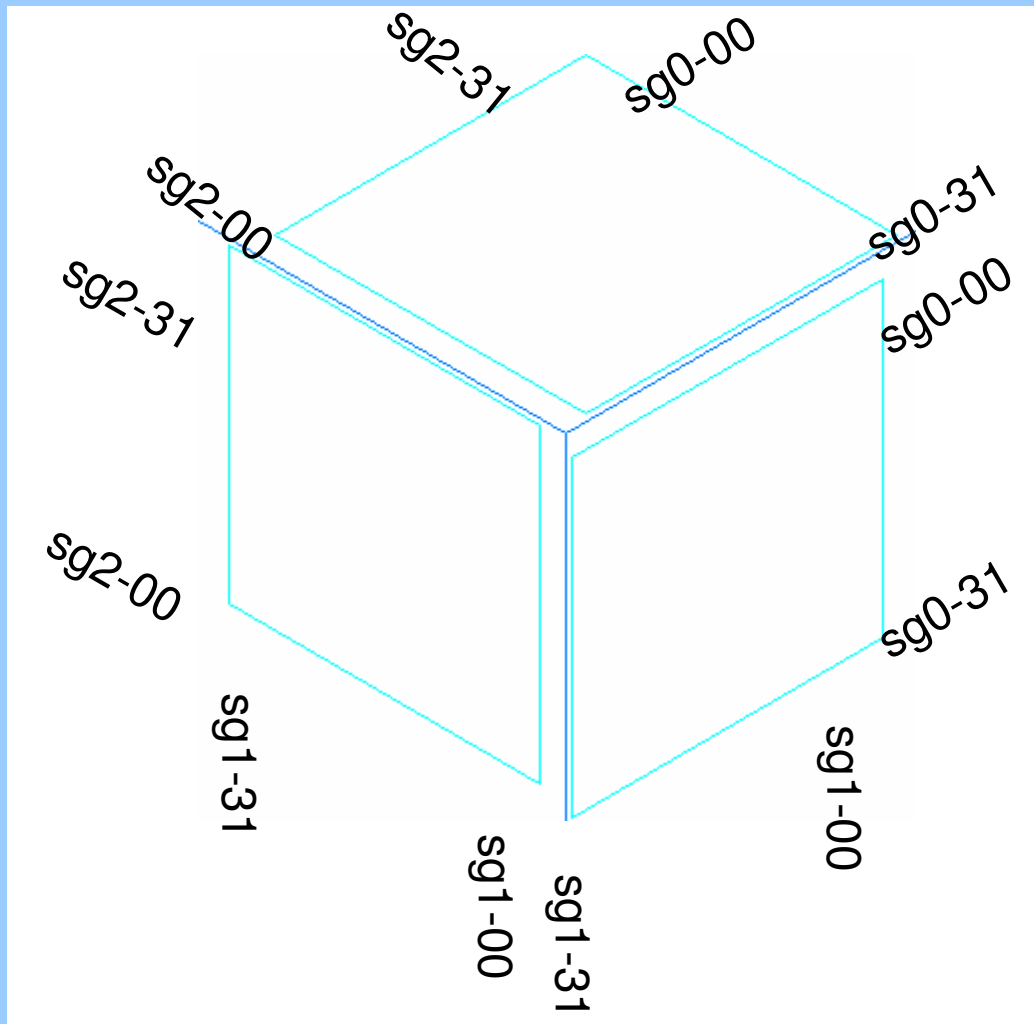
| | | | | | | | |
|--------|---------|------------|-----------------------------|-----------------------|-------------------------------|--------------|--------------------------|
| Drawn | Checked | Date | Tolerances Unless Stated | Outputs Via | Bartec Part Number | T8W104.08.L0 | Title |
| N.V.V. | S.W. | 04/11/2010 | Package OD ± 0.1 mm | Mating connector | Bartec Part Number | DS6-104.0.6 | LBL BB16 Right Hand PCB. |
| Des. | | | Package Hole ± 0.05 mm | Potted Wire Bonds | No | | 3D Assembly. |
| Appd. | | | Package Hole Pos'n ± 0.1 mm | Substrate Number | A-3648 | | Front and Rear View. |
| | | | Detector OD ± 20.0 µm | Substrate Material | 3.2 mm Thick FR4 PCB Material | | |
| | | | | Connector Orientation | Connector to Ext Rear Side | | |

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 Scale N/A Dims In .mm Dwg No C-2246

Another Paper Model



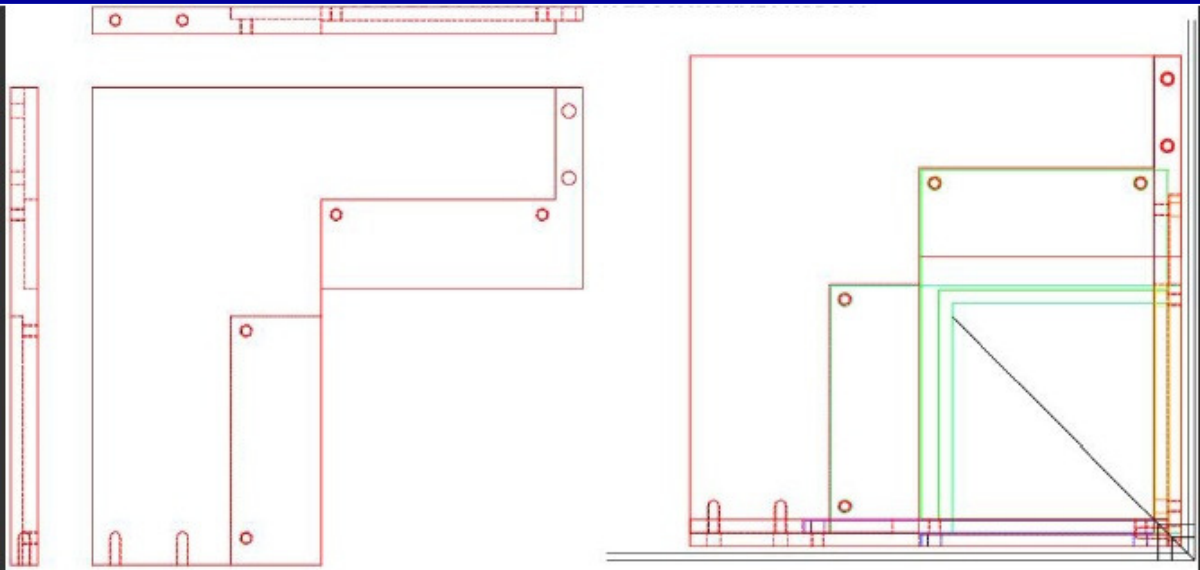
Strip Grouping in Focal Plane Array



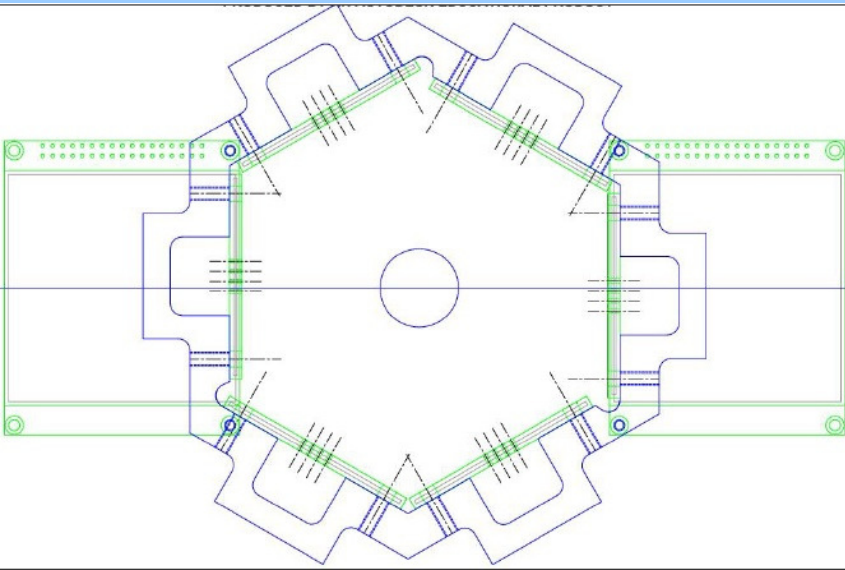
Signals are paired into three groups of 32 strips each.

Each event will have signals in two of the three strip groups. Provides unambiguous positions for 3072 pixels with a total of 96 signals.

Custom cabling solution from MESYTEC to eliminate “spaghetti” and improve gas purity inside BGS.

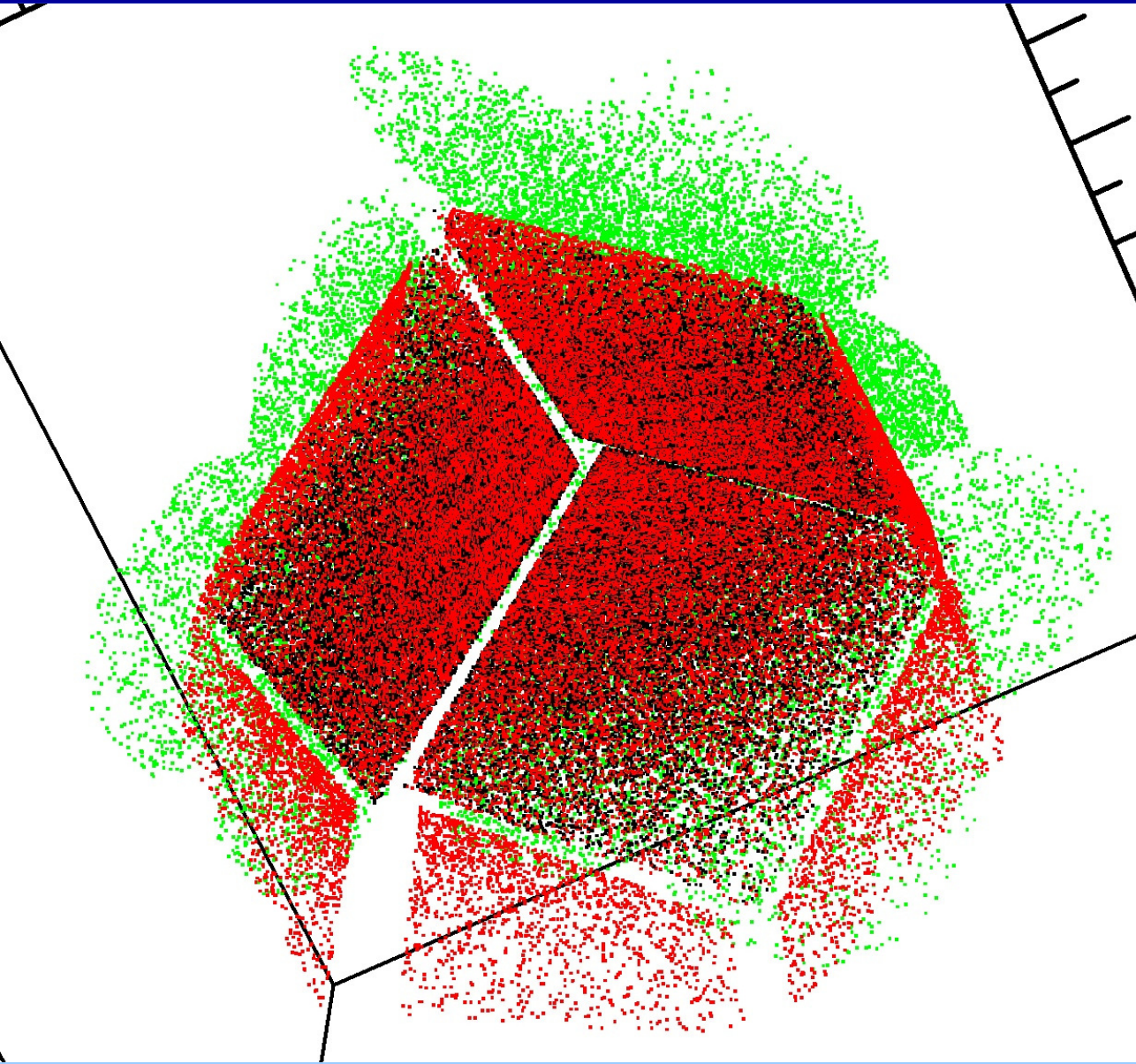


Focal plane and punchthru detector holder will be made from three identical pieces that bolt together to form the cube corner.



Upstream detector holder is a deformed hexagonal ring with capability to hold two of the Canberra 6cm x 6 cm PSDs as “wing” detectors to increase $B\rho$ coverage.

Efficiency Simulation



Recoils eff = 87%

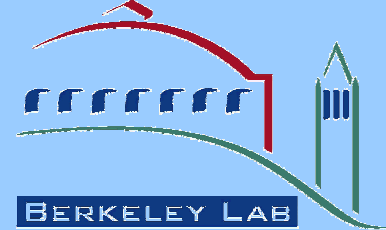
alphas eff = 92%

gamma solid angle = 50%

122 keV gammas eff = 30%

900 keV gammas eff = 7.5%

MESYTEC “Logarithmic” Preamplifiers and Two Amplifier Gain Ranges to Give Large Dynamic Range

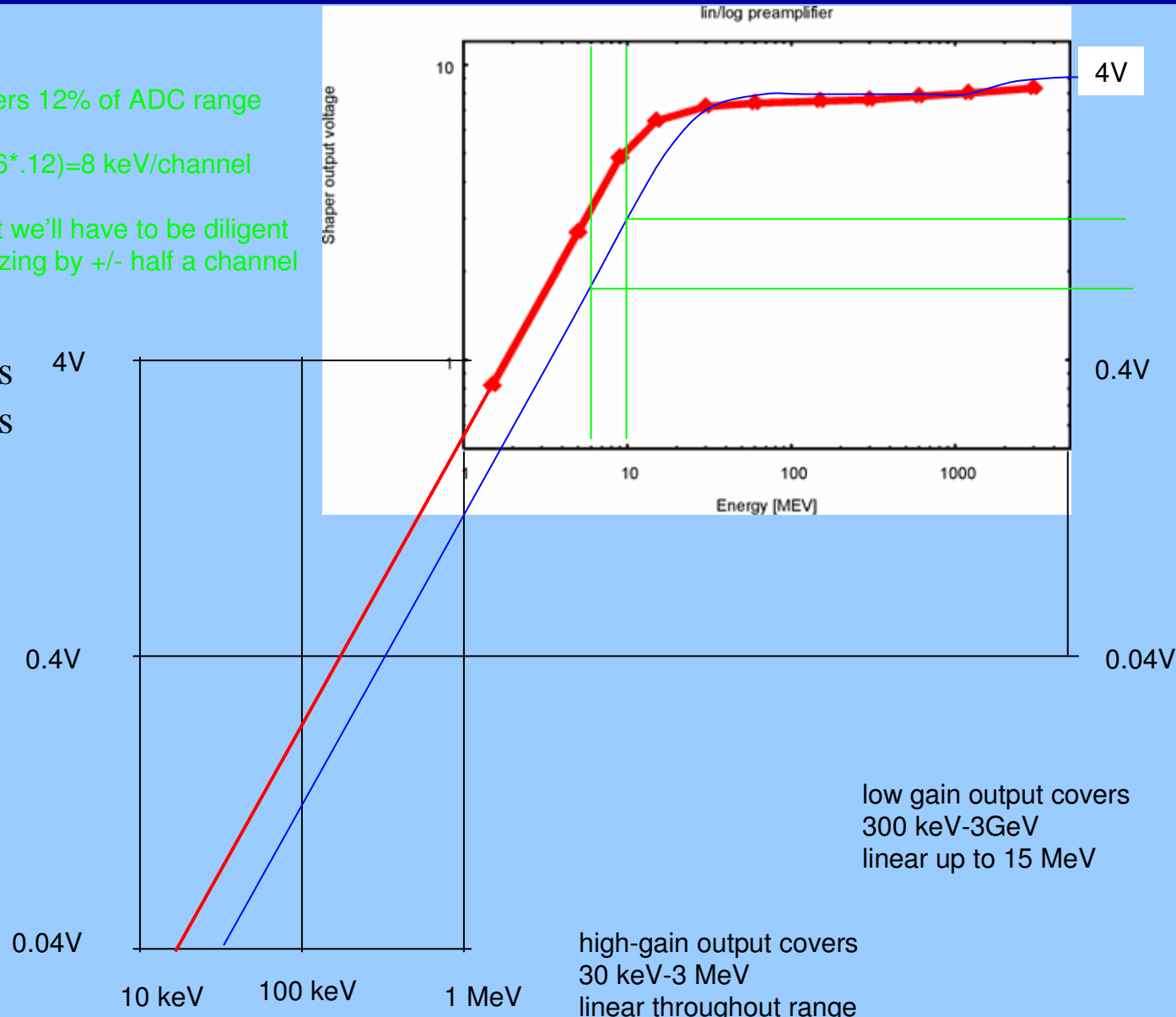


6-10 MeV covers 12% of ADC range
 $4000\text{keV}/(4096 \cdot .12) = 8 \text{ keV/channel}$
 This is OK, but we'll have to be diligent about randomizing by +/- half a channel

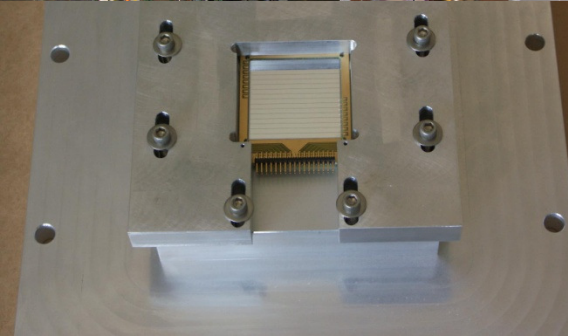
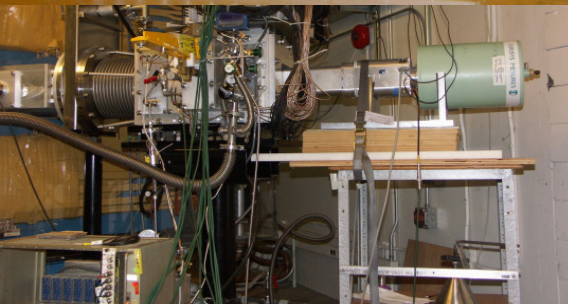
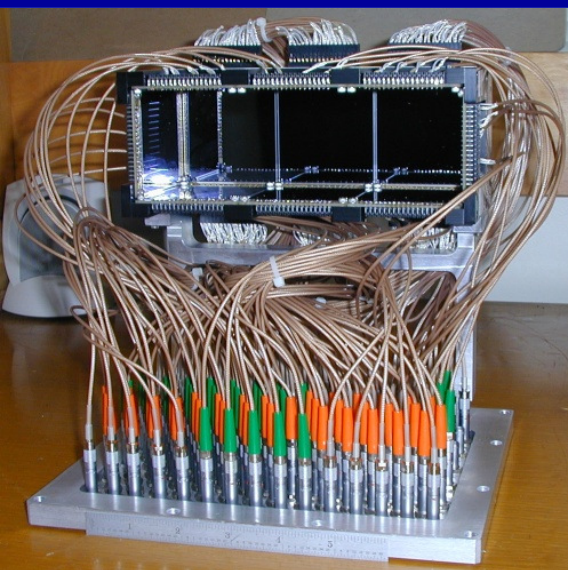
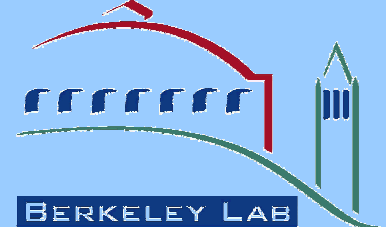
Analog DAQ:
 Mesytec logarithmic PAs
 CAEN N568B amplifiers
 MSU 1806 CFDs
 CAEN V785 ADCs
 CAEN V775 TDC
 SIS 3801, 3806 scalers

MBS software with
 home-baked `f_user.c`
 and `f_mbs_anal.c`

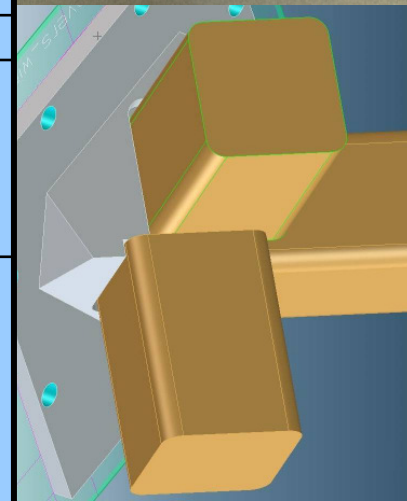
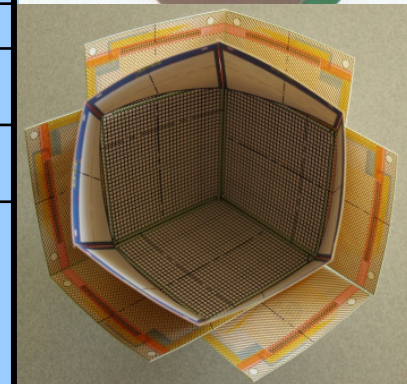
Minimum time between
 events $\sim 14 \mu\text{s}$



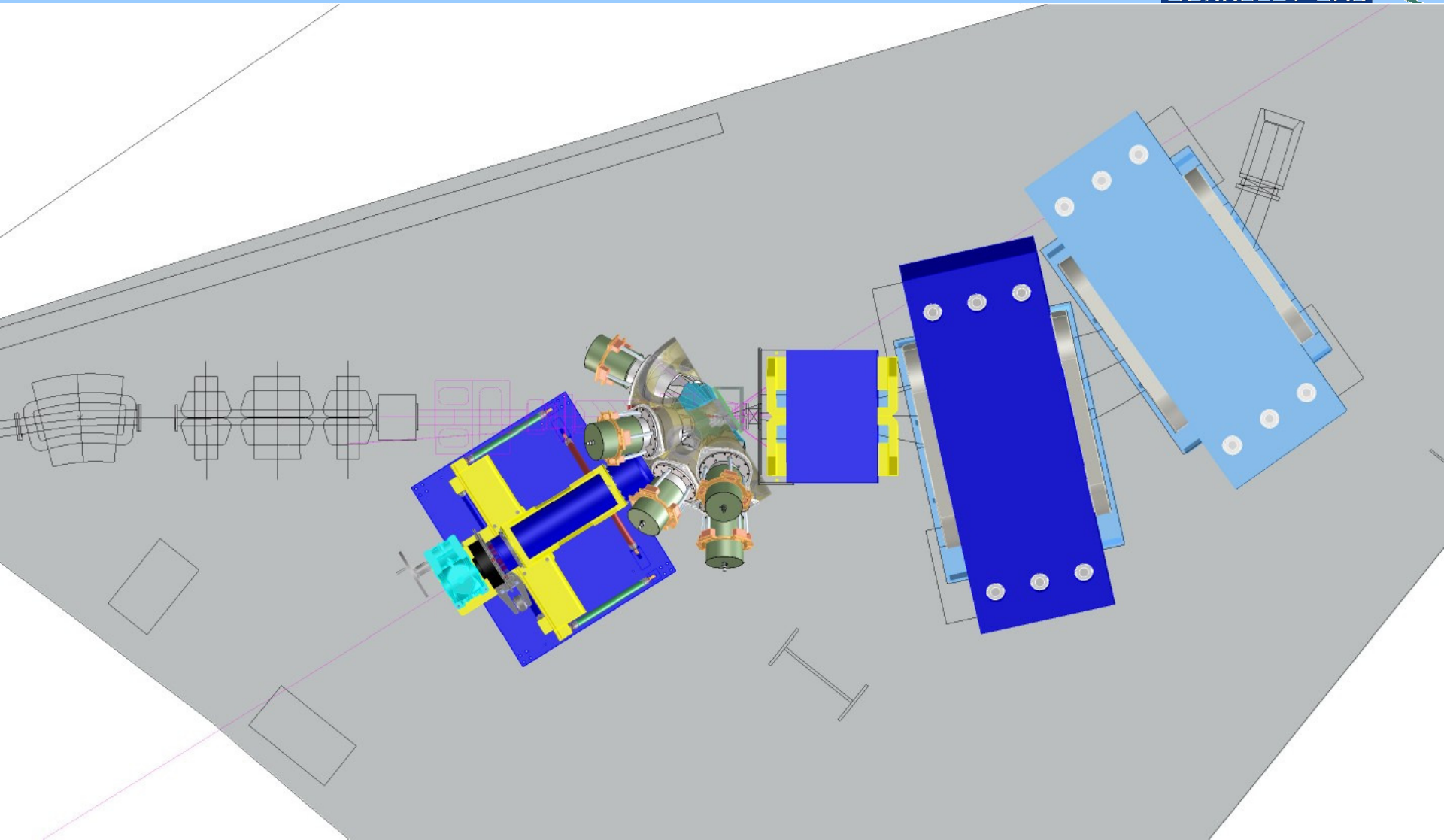
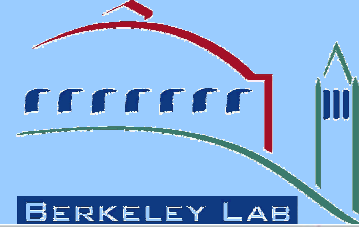
Efficiency gains with new DSSD configuration



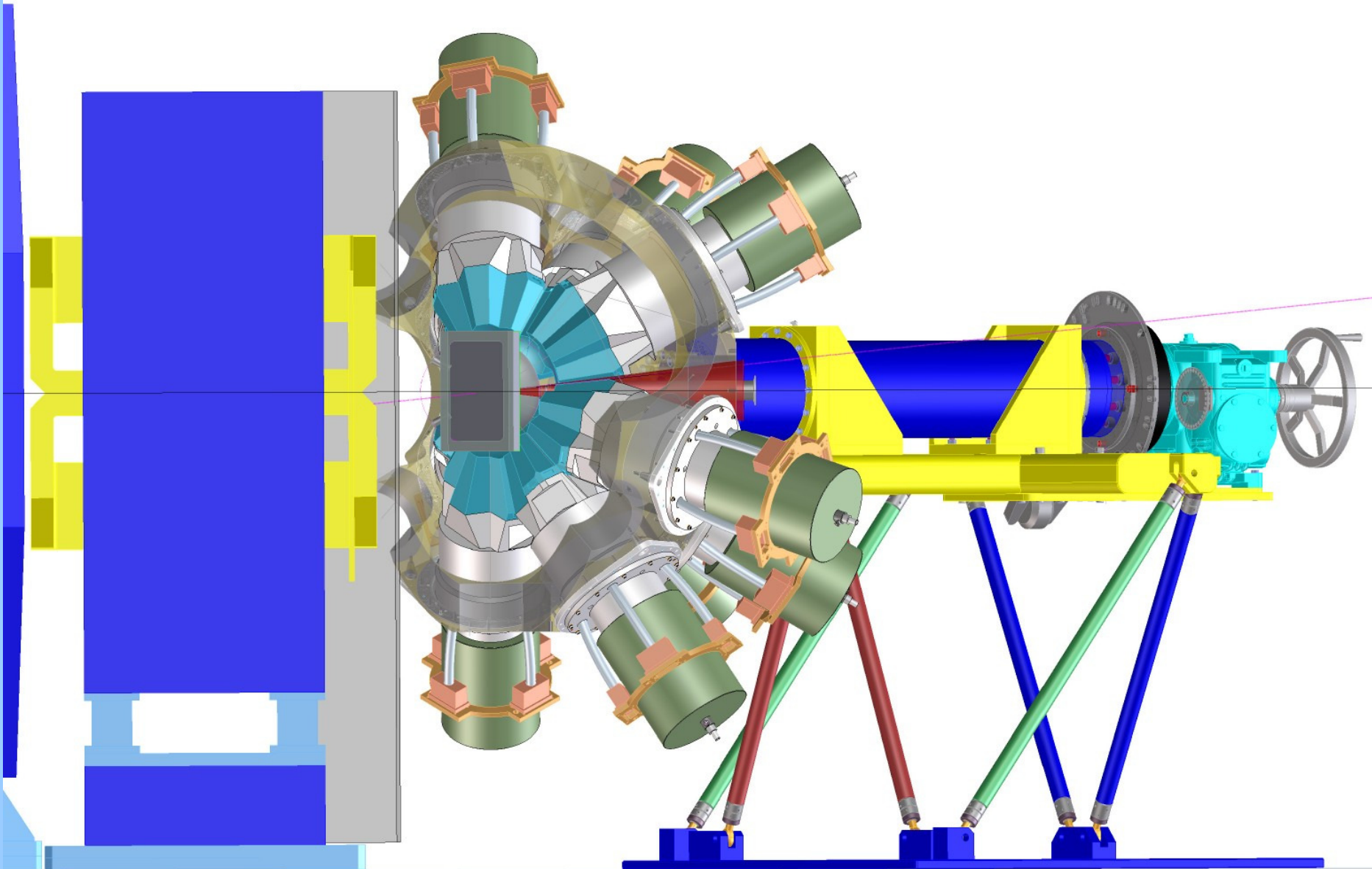
| event type | eff. 1 DSSD 1 clover | C ³ eff. 3 DSSDs 3 clovers | eff. gain |
|--|----------------------------|---|--------------|
| recoil | 35% | 87% | 2.48 |
| α | 50% | 92% | 1.84 |
| 122 keV Kx 900 keV γ | 16% 4.0% | 30% 7.5% | 1.88 |
| recoil- γ_{900} - α (K-isomer) | 0.7% | 6.0% | 8.6 |
| Recoil- α -Kx (SHE Z id.) | 2.8% | 24.% | 8.6 |



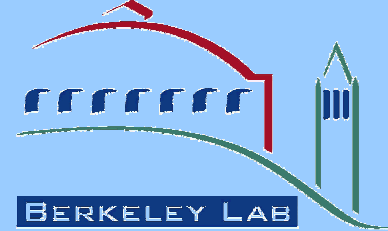
GRETINA@BGS Experiment Campaign, Fall 2011



Side view of GRETINA@BGS



GRETINA@BGS Experiments



DAQ test with $^{24}\text{Mg}^{5+}$ + something, $^{48}\text{Ca}^{10+}$ + ^{206}Pb

$^{24}\text{Mg}^{5+}$ is co-resonant with $^{48}\text{Ca}^{12+}$ for fast switching

High statistics $^{48}\text{Ca}^{11+}$ + ^{208}Pb

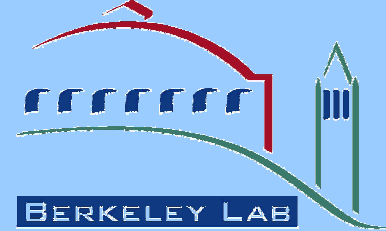
up to 100 x statistics compared to experiments at ANL, JYFL

In-beam spectroscopy with ^{50}Ti + ^{208}Pb

...

Interesting collaboration model

Mass Analysis Detector Facility Layout



C³ detector station

Trochoid separator

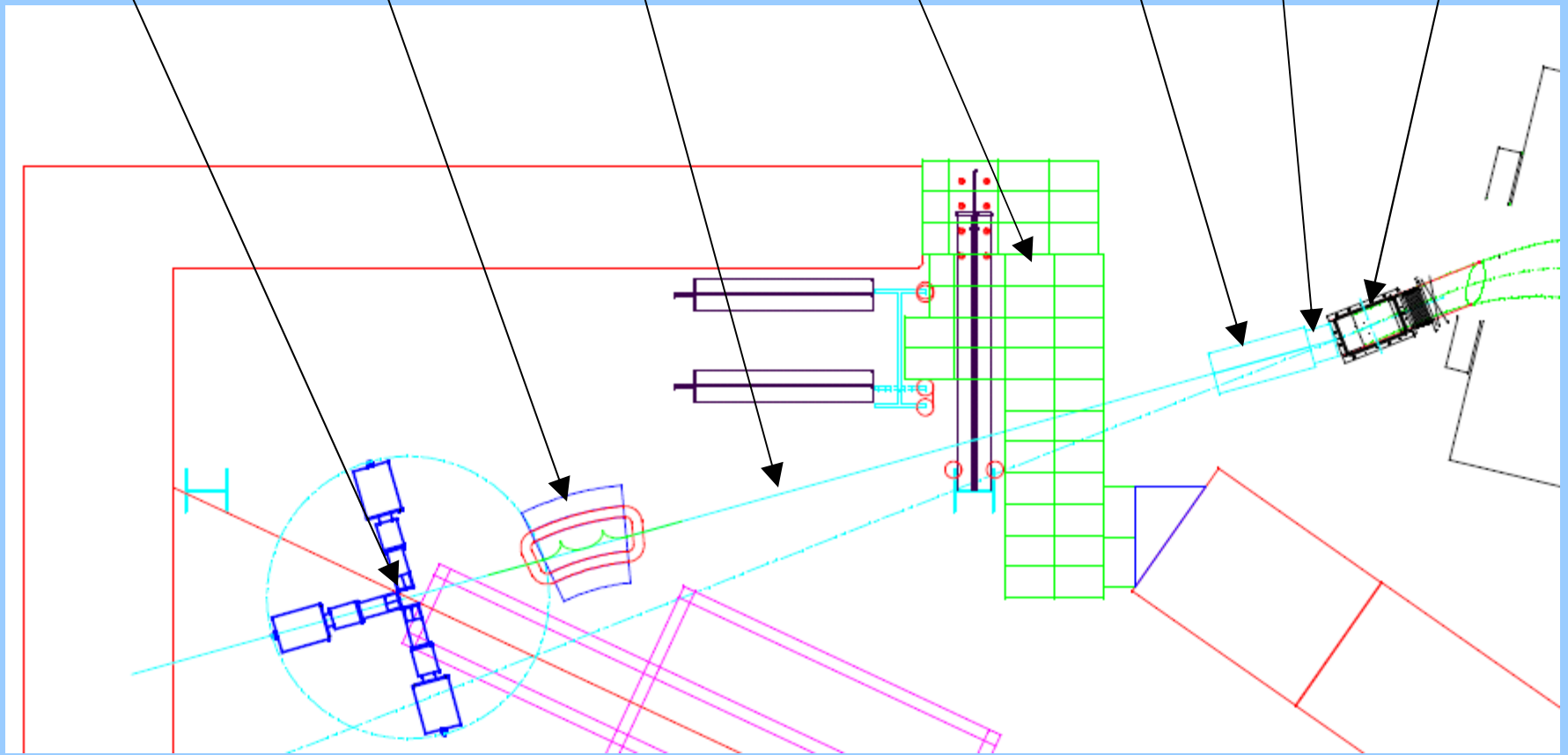
6⁰ beamline

re-configured cave wall

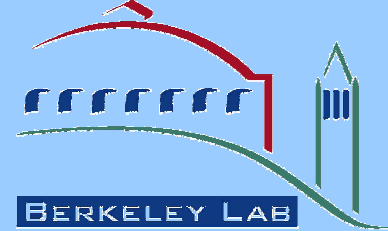
RFQ trap

RF catcher

BGS det. box



MADF Headline Experiment



Simultaneous determination of SHE A and Z:

Produce SHE in reaction such as $^{244}\text{Pu}(^{48}\text{Ca},3\text{n})^{289}114$

Isolate with Berkeley Gas-filled Separator

SHE ion passes through HAVAR window and stops in high-purity He (retains 1+ charge)

Focusing DC & RF field directs 1+ ion toward exit orifice, where it is carried by gas flow

Gas skimming and differential pumping results in “beam” of 1+ ions

1+ ions are trapped and cooled in RFQ trap

1+ ion is sent through trochiod mass analyzer for **determination of A**

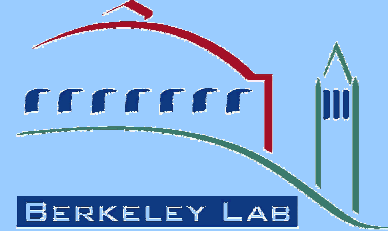
1+ ion is stopped in C³ detector system for measurement of α - γ coincidences

α -decay of odd-N SHE populates analog state in daughter.

Internal conversion of analog state γ -decay produces k X-ray

k X-ray of daughter is detected in coincidence with α -decay, **providing Z identification**

Mass separation and delivery to a low-background counting facility on a 10-ms timescale will enable a broad and enduring Nuclear Physics research program



Some Examples:

Determination of single-particle states in heavy and superheavy element isotopes will refine models of nuclear structure (Macroscopic-Microscopic, Hartree-Fock-Bogoliubov, Relativistic-Mean-Field).

Identification of spontaneous fission (SF) activities in the actinides and transactinides will clean up many of the questionable Z and A assignments, providing a more solid foundation for understanding SF systematics.

Identification of fission fragments can provide information on neutron multiplicity, fission fragment nuclear structure, and spin distribution in SF.

α - γ coincidence measurements can be used to measure nuclear structure and nuclear shapes in the region between the $N=152$ and $N=162$ deformed nuclear shells.

X-ray – γ coincidence measurements can be used to study electron-capture decay, providing low-lying nuclear structure information in neutron-deficient nuclides throughout the upper half of the nuclear chart.

Electron-capture-delayed fission and electron-capture to states above the fission barrier can provide information on fission barriers, fission isomers, and continuum states.